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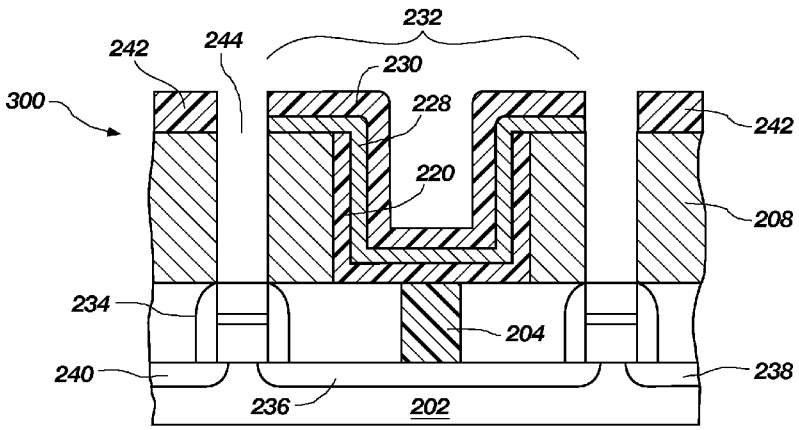


FIG. 3

(57) Abstract: Methods of selectively forming a conductive material and methods of forming metal conductive structures are disclosed. An organic material may be patterned to expose regions of an underlying material. The underlying material may be exposed to a precursor gas, such as a platinum precursor gas, that reacts with the underlying material without reacting with the remaining portions of the organic material located over the underlying material. The precursor gas may be used in an atomic layer deposition process, during which the precursor gas may selectively react with the underlying material to form a conductive structure, but not react with the organic material. The conductive structures may be used, for example, as a mask for patterning during various stages of semiconductor device fabrication.

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